150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor
19 November 2015 Product data sheet

# 1. General description

PNP high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBHV8515QA.

## 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FF</sub>) at high I<sub>C</sub>
- Low package height of 0.37 mm
- AEC-Q101 qualified
- Suitable for Automatic Optical Inspection (AOI) of solder joint

## 3. Applications

- LED driver for LED chain module
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-150	V
I <sub>C</sub>	collector current		-	-	-500	mA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	200	-	



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	E	emitter		В
3	С	collector	4 3	'*_
4	С	collector	2	sym132
			Transparent top view DFN1010D-3 (SOT1215)	

# 6. Ordering information

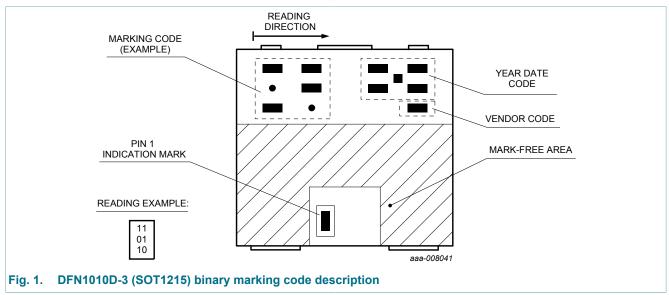
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV9515QA	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV9515QA	00 01 11



PBHV9515QA

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-150	V
$V_{CEO}$	collector-emitter voltage	open base		-	-150	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-500	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-1	Α
I <sub>BM</sub>	peak base current			-	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[ <u>3</u> ]	-	740	mW
			<u>[4]</u>	-	540	mW
			<u>[5]</u>	-	1	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

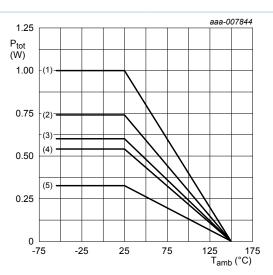
<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

<sup>[4]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

<sup>[5]</sup> Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig. 2. Power derating curves

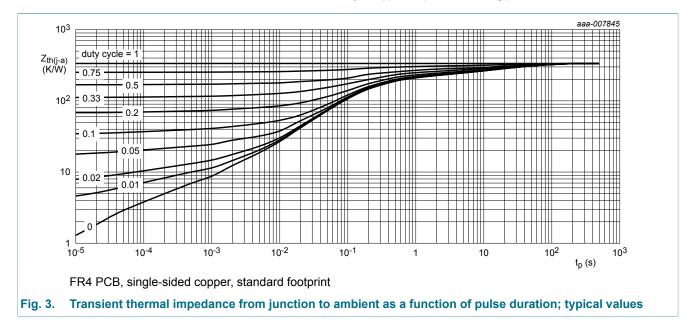
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## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	I I	[1]	-	-	385	K/W
	from junction to ambient		[2]	-	-	209	K/W
ambient	ambient		<u>[3]</u>	-	-	169	K/W
			[4]	-	-	232	K/W
			<u>[5]</u>	-	-	125	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



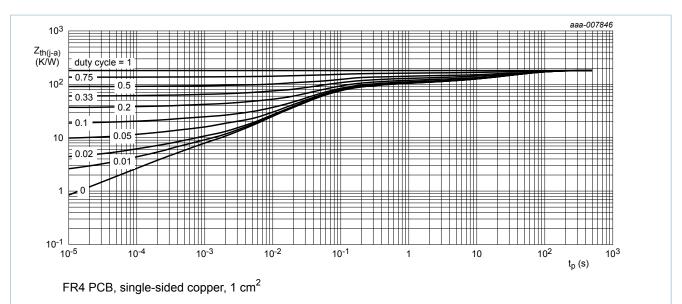


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

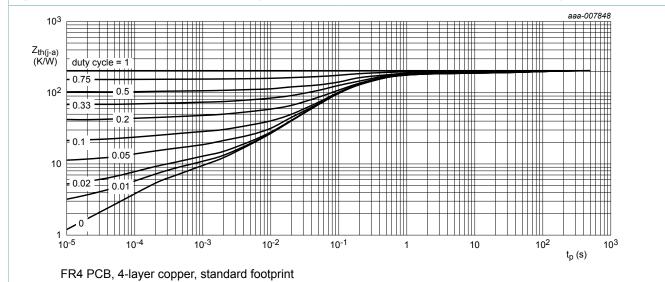
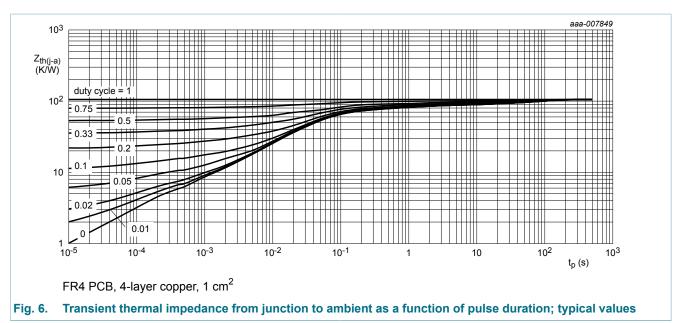


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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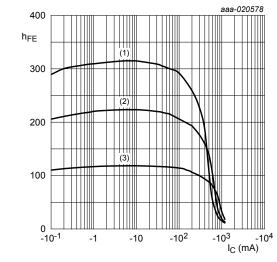
# 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-10	μΑ
ces	collector-emitter cut-off current	V <sub>CE</sub> = -120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub> DC current ga	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	210	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	200	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	190	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	70	135	-	
02001	collector-emitter	$I_C$ = -50 mA; $I_B$ = -5 mA; $T_{amb}$ = 25 °C	-	-65	-110	mV
	saturation voltage	$I_{C}$ = -100 mA; $I_{B}$ = -10 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-80	-140	mV
		$I_C$ = -100 mA; $I_B$ = -20 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-60	-110	mV
		$I_{C}$ = -200 mA; $I_{B}$ = -40 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-90	-160	mV
		I <sub>C</sub> = -500 mA; I <sub>B</sub> = -100 mA; pulsed;	-	-180	-300	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$t_p \le 300 \text{ μs; } δ \le 0.02; T_{amb} = 25 \text{ °C}$	-	-0.95	-1.2	V
d	delay time	V <sub>CC</sub> = -10 V; I <sub>C</sub> = -100 mA;	-	14	-	ns
r	rise time	I <sub>Bon</sub> = -20 mA; I <sub>Boff</sub> = 20 mA;	-	46	-	ns
ton	turn-on time	T <sub>amb</sub> = 25 °C	-	60	-	ns
ts	storage time		-	455	-	ns
f	fall time		-	105	-	ns
off	turn-off time		-	560	-	ns
fт	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	75	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	4.7	-	pF

## 150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 \text{ V}; I_C = 0 \text{ A}; i_C = 0 \text{ A};$	-	90	-	pF
		f = 1 MHz; T <sub>amb</sub> = 25 °C				



$$V_{CE}$$
 = -10  $V$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 7. DC current gain as a function of collector current; typical values

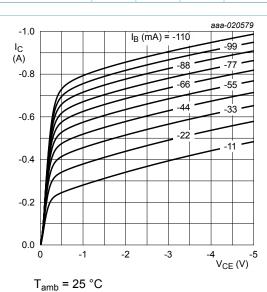
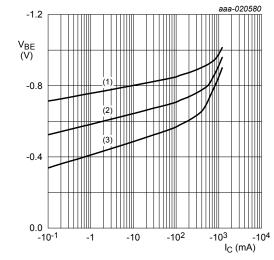


Fig. 8. Collector current as a function of collectoremitter voltage; typical values



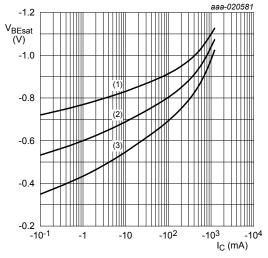
 $V_{CE}$  = -10 V

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 9. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

(1) 
$$T_{amb} = -55$$
 °C

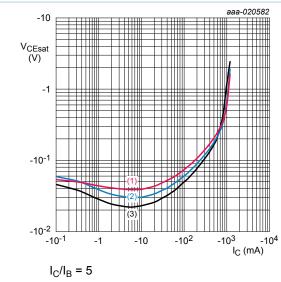
(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
= 100 °C

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

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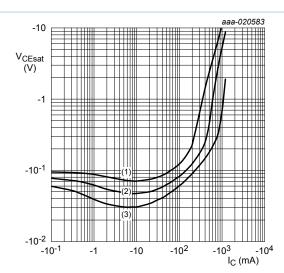


(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



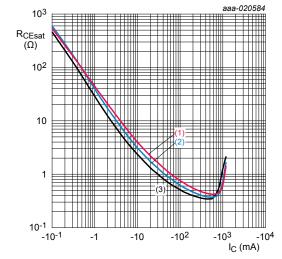
$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 20$$

(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



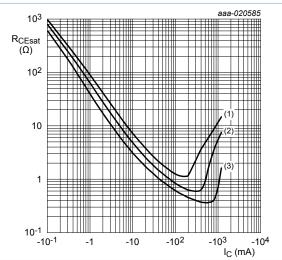
$$I_{\rm C}/I_{\rm B} = 5$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 20$$

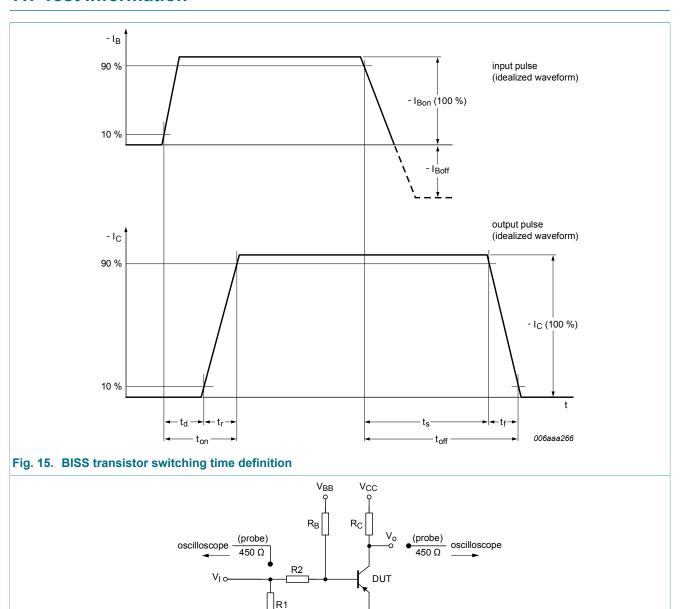
(2) 
$$I_C/I_B = 10$$

(3) 
$$I_C/I_B = 5$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

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## 11. Test information



## 11.1 Quality information

Fig. 16. Test circuit for switching times

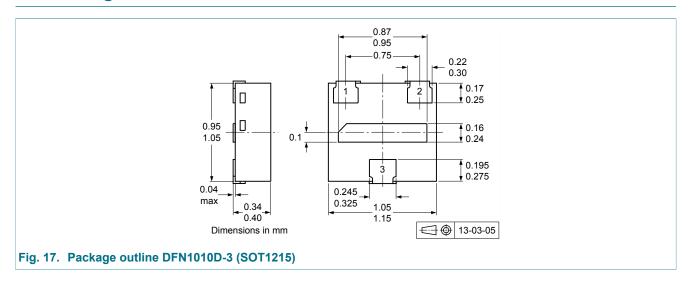
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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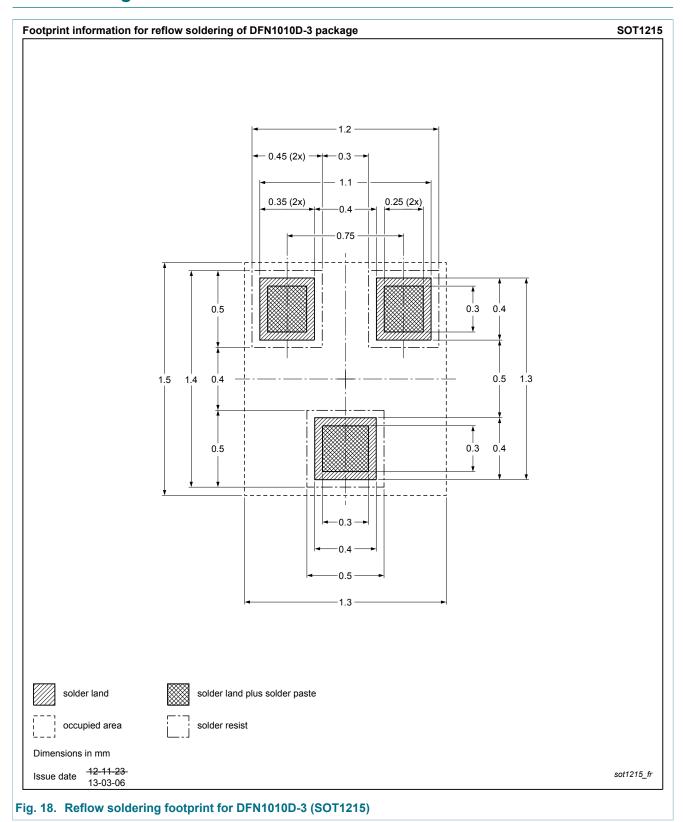
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# 12. Package outline



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# 13. Soldering



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# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9515QA v.1	20151119	Product data sheet	-	-

### 150 V, 500 mA PNP high-voltage low VCEsat (BISS) transistor

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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